

FEATURES

- Blue enhanced
- Low noise
- High shunt resistance
- High response

DESCRIPTION

Large area, instrumentation grade, blue enhanced silicon photodiode. Designed for low noise photovoltaic applications. Packaged in a BNC connector package.

APPLICATIONS

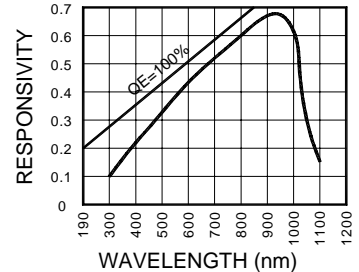
- Instrumentation
- Power meters
- Colorimeters
- Laser power meters

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		75	V
TS	Storage Temperature	-20	+70	°C
TO	Operating Temperature Range	-10	+60	°C
TS	Soldering Temperature*	N/A	N/A	°C
I _{max}	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ISC	Short Circuit Current	H = 100 fc, 2850 K	0.9	1.2		mA
ID	Dark Current	H = 0, VR = 10 mV		200	335	nA
RSH	Shunt Resistance	H = 0, VR = 10 mV	30	50		MΩ
TC RSH	RSH Temp. Coefficient	H = 0, VR = 10 mV		-8		% / °C
CJ	Junction Capacitance	H = 0, VR = 0V**		10,000	12,000	pF
I _{range}	Spectral Application Range	Spot Scan	350		1100	nm
I _p	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I = 10 μA	20	30		V
NEP	Noise Equivalent Power	VR = 10 mV @ Peak		2x10 ⁻¹⁴		W/ √Hz
tr	Response Time	RL = 1 KΩ VR = 0V		2000		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz